

Docket No. 206405US-2



IN RE APPLICATION OF: HIROSHI NISHIMORI, ET AL.

SERIAL NO: 09/845,272

FILED: MAY 1, 2001

FOR: POWER SEMICONDUCTOR DEVICE

ASSISTANT COMMISSIONER FOR PATENTS

WASHINGTON, D.C. 20231

SIR:

Transmitted herewith is an amendment in the above-identified application.

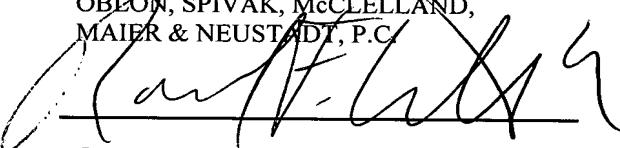
- No additional fee is required
- Small entity status of this application under 37 C.F.R. §1.9 and §1.27 has been established by a verified statement previously submitted.
- Small entity status of this application under 37 C.F.R. §1.9 and §1.27 has been established by a verified statement submitted herewith.
- Additional documents filed herewith: MARKED-UP COPY

The Fee has been calculated as shown below:

CLAIMS	CLAIMS REMAINING		HIGHEST NUMBER PREVIOUSLY PAID	NO. EXTRA CLAIMS	RATE	CALCULATIONS
TOTAL	10	MINUS	20	0	× \$18 =	\$0.00
INDEPENDENT	2	MINUS	3	0	× \$84 =	\$0.00
		<input type="checkbox"/> MULTIPLE DEPENDENT CLAIMS		+ \$280 =		\$0.00
						\$0.00
		<input type="checkbox"/> Reduction by 50% for filing by Small Entity				\$0.00
		<input type="checkbox"/> Recordation of Assignment		+ \$40 =		\$0.00
						TOTAL \$0.00

- A check in the amount of \$ -0- is attached.
- Please charge any additional Fees for the papers being filed herewith and for which no check is enclosed herewith, or credit any overpayment to deposit Account No. 15-0030. A duplicate copy of this sheet is enclosed.
- If these papers are not considered timely filed by the Patent and Trademark Office, then a petition is hereby made under 37 C.F.R. §1.136, and any additional fees required under 37 C.F.R. §1.136 for any necessary extension of time may be charged to Deposit Account No. 15-0030. A duplicate copy of this sheet is enclosed.

OBLON, SPIVAK, McCLELLAND,
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206405US



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MAY 29/02

IN THE UNITED STATES PATENT & TRADEMARK OFFICE

IN RE APPLICATION OF: :

HIROSHI NISHIBORI ET AL. : GROUP ART UNIT: 2827

SERIAL NO: 09/845,272 :

FILED: MAY 1, 2001 : EXAMINER: CRUZ, L.

FOR: POWER SEMICONDUCTOR
DEVICE

AMENDMENT

ASSISTANT COMMISSIONER FOR PATENTS
WASHINGTON, D.C. 20231

SIR:

In response to the Office Action mailed on March 21, 2002, please amend the above-identified application as follows:

RECEIVED
JUN 24 2002
TECHNOLOGY CENTER 2800

IN THE SPECIFICATION

Please amend the specification as follows:

~~Please replace the paragraph beginning on page 1, line 25 to page 2, line 7, with the following text:~~

a!
When a Cu alloy is used as the material for the circuit pattern and the lower pattern, there is a high probability of cracks forming in the insulating substrate and the soldering layer in an early stage due to a temperature cycle. As a countermeasure for this problem, Al/SiC and Cu/Mo may be used as the materials for the metal base plate instead of Cu as these materials have coefficients of expansion closer to that of the ceramics being used.